TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR ILICON PLANAR TYPE

# **SM25GZ51, SM25JZ51**

### AC POWER CONTROL APPLICATIONS

- Repetitive Peak Off-State Voltage: VDRM = 400V, 600V
- R.M.S On-State Current: IT (RMS) = 25A
- High Commutating (dv / dt): (dv / dt)  $c = 10V / \mu s$
- Isolation Voltage: V<sub>Isol</sub> = 1500V AC

#### **ABSOLUTE MAXIMUM RATINGS**

CHARACTERISTIC		SYMBOL	RATING	THAU	
Repetitive Peak Off-State Voltage	SM25GZ51	$V_{DRM}$	400	$( \bigcirc / \land )$	
	SM25JZ51	V DRM	600	VV	
R.M.S On-State Currer (Full Sine Waveform To	• •	I <sub>T (RMS)</sub>	25	A	
Peak One Cycle Surge On-State Current (Non-Repetitive)		I <sub>TSM</sub>	230 (50Hz)	A	
		TSM	253 (60Hz)		
I <sup>2</sup> t Limit Value		I <sup>2</sup> t	260	A <sup>2</sup> s	
Critical Rate of Rise of On-State Current	(Note 1)	di / dt 50		A/µs	
Peak Gate Power Dissi	pation	P <sub>GM</sub>	5	W	
Average Gate Power Di	ssipation	PG (AV)	0.5	w	
Peak Gate Voltage		(V <sub>GM</sub> )) 10		//v	
Peak Gate Current		IGM	2	A	
Junction Temperature		// )Tj	-40~125	°C	
Storage Temperature R	ange	T <sub>stg</sub>	-40~125	°C	
Isolation Voltage (AC, t	= 1 min.)	○ V <sub>Isol</sub>	1500	V	

Weight: 5.9 g (typ.)

Note 1: di / dt Test Condition V<sub>DRM</sub> = 0.5 × Rated

I<sub>TM</sub> ≤ 40Å

t<sub>qw</sub> ≥ 10µs

t<sub>gr</sub> ≤ 250ns

 $i_{gp} \neq i_{GT} \times 2.0$ 

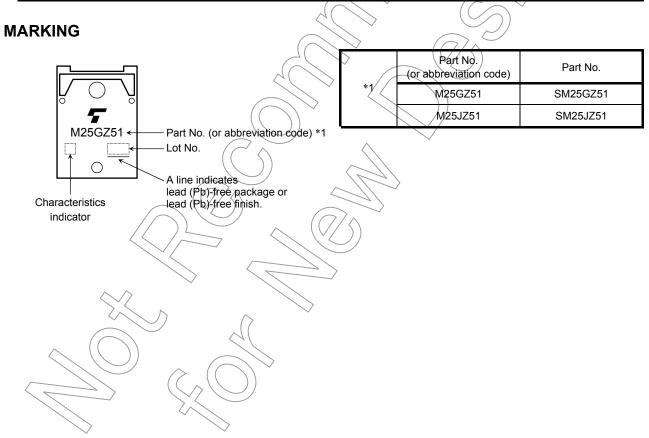
Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

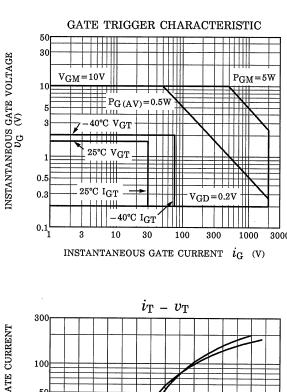
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

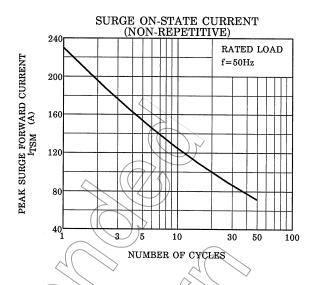


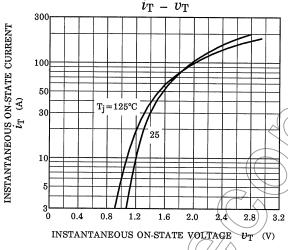
## **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

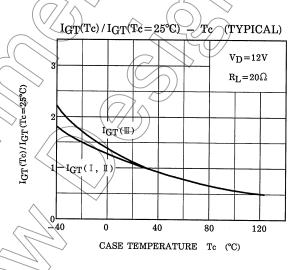
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT
Repetitive Peak Off-State Current		I <sub>DRM</sub>	V <sub>DRM</sub> = Rated		_	_	20	μA
Gate Trigger Voltage	I		V <sub>D</sub> = 12V R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)	-	_	1.5	V
	II	V <sub>GT</sub>		T2 (+) , Gate (-)	/	_	1.5	
	III			T2 (-) , Gate (-)		1	1.5	
Gate Trigger Current	I	I <sub>GT</sub>	V <sub>D</sub> = 12V R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)		) }_	30	mA
	П			T2 (+) , Gate (-)	<u> </u>	_	30	
	III			T2 (-), Gate (-)	$\bigcirc )$	_	30	
Peak On-State Voltage		$V_{TM}$	I <sub>TM</sub> = 40A		)	-	1.5	٧
Gate Non-Trigger Voltage		$V_{GD}$	V <sub>D</sub> = Rated, Tc = 125°C		0.2	-	_	٧
Holding Current		lΗ	V <sub>D</sub> = 12V, I <sub>TM</sub> = 1A		_		60	mA
Thermal Resistance		R <sub>th (j-c)</sub>	Junction to Case, AC		- /	4	1.3	°C / W
Critical Rate of Rise of Off-State Voltage		dv / dt	V <sub>DRM</sub> = Rated T <sub>V</sub> = 125°C Exponential Rise		-(	300	> _	V / µs
Critical Rate of Rise of Off-State Voltage at Commutation		(dv / dt) c	V <sub>DRM</sub> = 400V, (di / dt) c = -1!	(10/	D	_	V / µs	

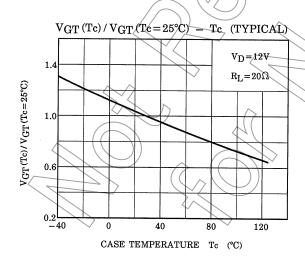


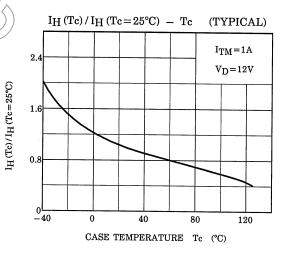




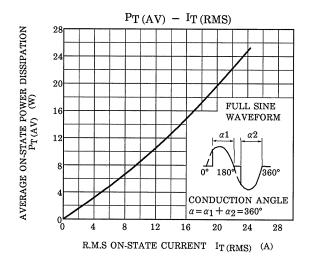


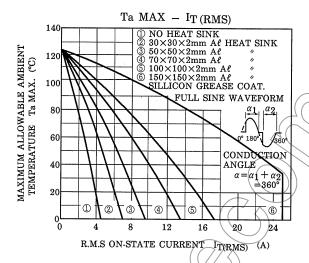


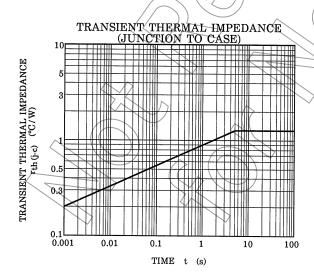


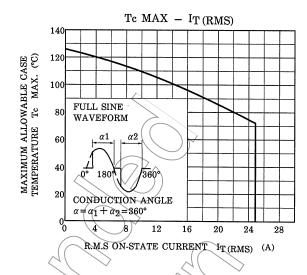


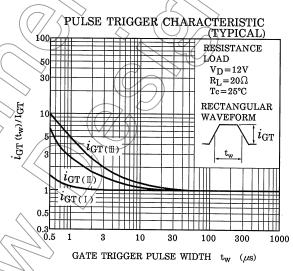
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